

N-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A) ^a		
60	0.0018 at $V_{GS} = 10 \text{ V}$	180		
00	0.0028 at $V_{GS} = 4.5 \text{ V}$	155		

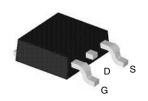
FEATURES

- DT-Trench Power MOSFET
- 100 % R_g and UIS Tested

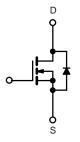


COMPLIANT

TO-252 Pin Configuration



Top View

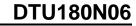


N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
Parameter		Symbol	Limit	Unit	
Gate-Source Voltage	V _{GS}	± 20	V		
Continuous Drain Current (T _{.I} = 175 °C) ^b	T _C = 25 °C	1-	180		
Continuous Diam Current (1, = 175°C)	T _C = 100 °C	l I _D	135 ^a		
Pulsed Drain Current	I _{DM}	720	Α		
Continuous Source Current (Diode Conduction)	I _S	180ª			
Avalanche Current	I _{AS}	150			
Single Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH	E _{AS}	330	mJ	
Maximum Power Dissipation	T _C = 25 °C	P _D	255	w	
Maximum Fower Dissipation	T _A = 25 °C	' b	6.9 ^b	VV	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Mariania lugation to Ambienta	t ≤ 10 sec	R _{thJA}	8	15		
Maximum Junction-to-Ambient ^a	Steady State	' thJA	12	45	°C/W	
Maximum Junction-to-Case		R _{thJC}	0.9	1.5		

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- $c.\ t \leq 10\ s.$





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Static	SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)							
Drain-Source Breakdown Voltage V _{DS} V _{GS} = 0 V, I _D = 250 μA 60 V Gate Threshold Voltage V _{GS} (th) V _{DS} = V _{GS} , I _D = 250 μA 1 - 3 Gate-Body Leakage I _{GSS} V _{DS} = 0 V, V _{GS} = ± 20 V ± 100 nA Zero Gate Voltage Drain Current I _{DSS} V _{DS} = 48 V, V _{GS} = 0 V 1 1 V _{DS} = 48 V, V _{GS} = 0 V, T _J = 175 °C 50 250 250 On-State Drain Current ^b I _{D(on)} V _{DS} = 5 V, V _{GS} = 10 V 180 A Drain-Source On-State Resistance ^b R _{DS(on)} V _{DS} = 5 V, V _{DS} = 10 V, I _D = 20 A 0.0018 0.0026 V _{GS} = 10 V, I _D = 20 A 0.0023 0.0032 0.0032 Drain-Source On-State Resistance ^b 9fs V _{DS} = 48 V, I _D = 20 A 0.0018 0.0026 V _{GS} = 10 V, I _D = 20 A 0.0023 0.0032 0.0032 0.0032 0.0032 Drain-Source On-State Resistance ^b 9fs V _{DS} = 48 V, I _D = 20 A 175 S S Dynamic 1 1 1 1 0.0023			Min.	Typ. ^a	Max.	Unit		
Gate Threshold Voltage	Static							
Gate Threshold Voltage V _{GS(th)} V _{DS} = V _{SS} , I _D = 250 µA 1 - 3	rain-Source Breakdown Voltage V _{DS}		$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	60	60		.,	
Vos = 48 V, Vos = 0 V	Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1	-	3	V	
	Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
V _{DS} = 48 V, V _{GS} = 0 V, T _J = 175 °C 250			V _{DS} = 48 V, V _{GS} = 0 V	V _{DS} = 48 V, V _{GS} = 0 V		1	μA	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 48 V, V _{GS} = 0 V, T _J = 125 °C			50		
$ P_{OS} = 10 \ V. \ _{D} = 20 \ A \\ P_{OS} = 10 \ V. \ _{D} = 20 \ A \\ P_{OS} = 10 \ V. \ _{D} = 20 \ A \\ P_{OS} = 10 \ V. \ _{D} = 20 \ A \\ P_{OS} = 10 \ V. \ _{D} = 20 \ A \\ P_{OS} = 10 \ V. \ _{D} = 15 \ A \\ P_{OS} = 10 \ V. \ _{D} = 15 \ A \\ P_{OS} = 10 \ V. \ _{D} = 15 \ A \\ P_{OS} = 10 \ V. \ _{D} = 15 \ A \\ P_{OS} = 10 \ V. \ _{D} = 15 \ A \\ P_{OS} = 10 \ V. \ _{D} = 15 \ A \\ P_{OS} = 10 \ V. \ _{D} = 15 \ A \\ P_{OS} = 10 \ V. \ _{D} = 15 \ A \\ P_{OS} = 10 \ V. \ _{D} = 15 \ A \\ P_{OS} = 10 \ V. \ _{D} = 15 \ A \\ P_{OS} = 10 \ V. \ _{D} = 15 \ A \\ P_{OS} = 10 \ V. \ _{D} = 15 \ A \\ P_{OS} = 10 \ V. \ _{D} = 15 \ A \\ P_{OS} = 10 \ V. \ _{D} = 15 \ A \\ P_{OS} = 10 \ V. \ _{D} = 15 \ A \\ P_{OS} = 10 \ V. \ _{D} = 15 \ A \\ P_{OS} = 10 \ V. \ _{D} = 15 \ A \\ P_{OS} = 10 \ V. \ _{D} = 10 \ A \\ P_{OS} = 10 \ P$			V _{DS} = 48 V, V _{GS} = 0 V, T _J = 175 °C			250	1	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	180			Α	
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$			V _{GS} = 10 V, I _D = 20 A		0.0018	0.0026		
$V_{GS} = 10 \text{ V, } I_D = 15 \text{ A, } I_J = 173 \text{ C} \\ V_{GS} = 4.5 \text{ V, } I_D = 15 \text{ A} \\ 0.0028 0.0039 \\ \hline \\ V_{GS} = 4.5 \text{ V, } I_D = 15 \text{ A} \\ 0.0028 0.0039 \\ \hline \\ V_{DS} = 48 \text{ V, } I_D = 20 \text{ A} \\ \hline \\ Dynamic \\ \hline \\ Dutput Capacitance \\ C_{ISS} \\ Cotal Gate Chargec \\ C_{Oss} \\ Cotal Gate Chargec \\ C_{Qg} \\ Cate-Source Chargec \\ C_{Qg} \\ Cate-Drain Chargec \\ C_{Qg} \\ Cate-Drain Chargec \\ C_{Qg} \\ Cate-Drain Chargec \\ C_{Qg} \\ C_{DS} \\ Cate-Drain Chargec \\ C_{DS} \\ C_{DS$	5 : 0	D	V _{GS} = 10 V, I _D =20 A, T _J = 125 °C		0.0023	0.0032	Ω	
Forward Transconductance ^b g_{fs} $V_{DS} = 48 \text{ V}, I_D = 20 \text{ A}$ 175 S Dynamic Input Capacitance C_{iss} 11050 11050 pF Output Capacitance C_{oss} $V_{GS} = 0 \text{ V}, V_{DS} = 48 \text{ V}, f = 1 \text{ MHz}$ 1650 pF Reverse Transfer Capacitance C_{rss} 185 79 79 79 79 79 79 79 79 70	Drain-Source On-State Resistance	NDS(on)	V _{GS} = 10 V, I _D =15 A, T _J = 175 °C		0.0029	0.0042		
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$			V _{GS} = 4.5 V, I _D = 15 A		0.0028	0.0039		
$ \begin{array}{ c c c c c c } \hline \text{Input Capacitance} & C_{iss} \\ \hline \text{Output Capacitance} & C_{oss} \\ \hline \text{Reverse Transfer Capacitance} & C_{rss} \\ \hline \hline \text{Total Gate Charge}^c & Q_g \\ \hline \text{Gate-Source Charge}^c & Q_{gs} \\ \hline \text{Gate-Drain Charge}^c & Q_{gd} \\ \hline \text{Turn-On Delay Time}^c & t_d \\ \hline \text{Turn-Off Delay Time}^c & t_d \\ \hline \text{Fall Time}^c & t_f \\ \hline \text{Source-Drain Diode Ratings and Characteristics } (T_C = 25 ^{\circ}\text{C}) \\ \hline \text{Pulsed Current} & I_{SM} \\ \hline \text{Diode Forward Voltage} & C_{oss} \\ \hline \hline \text{V}_{QS} = 0 \text{V}, \text{V}_{DS} = 48 \text{V}, \text{V}_{GS} = 10 \text{V}, \text{I}_{D} = 20 \text{A} \\ \hline \text{11050} \\ \hline \text{1650} \\ \hline \text{1660} \\ \hline \text{166} \\ \hline \text{11050} \\ \hline \text{1660} \\ \hline \text{11050} \\ \hline 1$	Forward Transconductance ^b	9 _{fs}	$V_{DS} = 48 \text{ V}, I_{D} = 20 \text{ A}$		175		S	
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	Dynamic							
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Input Capacitance	C _{iss}			11050			
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 48 \text{ V}, f = 1 \text{ MHz}$		1650		pF	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Reverse Transfer Capacitance	C _{rss}			185			
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Total Gate Charge ^c	Q_g			79			
Turn-On Delay Time ^c $t_{d(on)}$ Rise Time ^c t_r $V_{DD} = 48 \text{ V}, R_L = 0.6 \Omega$ Turn-Off Delay Time ^c $t_d(off)$ Fall Time ^c t_f $I_D \cong 20 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 2.5 \Omega$ Source-Drain Diode Ratings and Characteristics ($T_C = 25 \text{ °C}$) Pulsed Current I_{SM} $T_{CD} = 20 \text{ A}, V_{GS} = 0 \text{ V}$ $T_{CD} = 20 \text{ A}$ Diode Forward Voltage $T_r = 20 \text{ A}, V_{GS} = 0 \text{ V}$ $T_{CD} = 20 \text{ A}$	Gate-Source Charge ^c	Q_{gs}	$V_{DS} = 48 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$		16		nC	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Gate-Drain Charge ^c	Q_{gd}			20			
Turn-Off Delay Time ^c $t_{d(off)}$ $I_D \cong 20 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 2.5 \Omega$ 68 Fall Time ^c t_f 15 Source-Drain Diode Ratings and Characteristics ($T_C = 25 \text{ °C}$) Pulsed Current I_{SM} 720 A Diode Forward Voltage V_{SD} $I_F = 20 \text{ A}, V_{GS} = 0 \text{ V}$ 1.25 V	Turn-On Delay Time ^c	t _{d(on)}			20			
Turn-Off Delay Time ^c $t_{d(off)}$ $I_D \cong 20 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 2.5 \Omega$ 68 Fall Time ^c t_f 15 Source-Drain Diode Ratings and Characteristics ($T_C = 25 \text{ °C}$) Pulsed Current I_{SM} 720 A Diode Forward Voltage V_{SD} $I_F = 20 \text{ A}, V_{GS} = 0 \text{ V}$ 1.25 V	Rise Time ^c	t _r	DD		35		ns	
Source-Drain Diode Ratings and Characteristics ($T_C = 25$ °C)Pulsed Current I_{SM} 720ADiode Forward Voltage V_{SD} $I_F = 20 \text{ A}, V_{GS} = 0 \text{ V}$ 1.25V	Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 20 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 2.5 \Omega$		68			
Pulsed Current I_{SM} 720ADiode Forward Voltage V_{SD} $I_F = 20 \text{ A}, V_{GS} = 0 \text{ V}$ 1.25V	Fall Time ^c	t _f			15			
Diode Forward Voltage V_{SD} $I_F = 20 \text{ A}, V_{GS} = 0 \text{ V}$ 1.25 V	Source-Drain Diode Ratings and Characteristics (T _C = 25 °C)							
	Pulsed Current					720	Α	
Reverse Recovery Time t_{rr} $I_F = 20 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}$ 73 ns	Diode Forward Voltage	V _{SD}				1.25	V	
	Reverse Recovery Time	t _{rr}	$I_F = 20 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}$		73		ns	

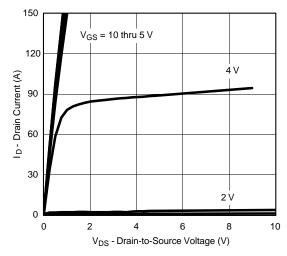
Notes:

- a. For design aid only; not subject to production testing.
- b. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- c. Independent of operating temperature.

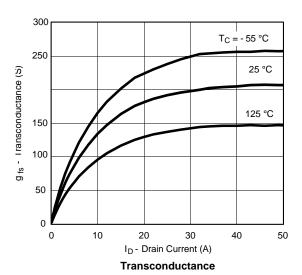
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

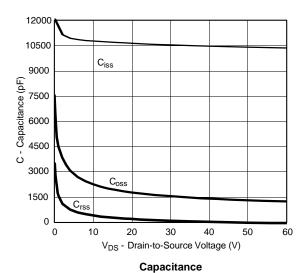


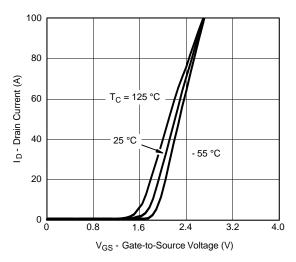
TYPICAL CHARACTERISTICS (25 °C unless noted)



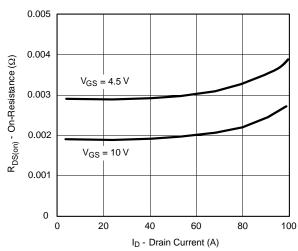
Output Characteristics



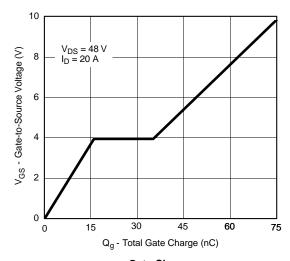




Transfer Characteristics



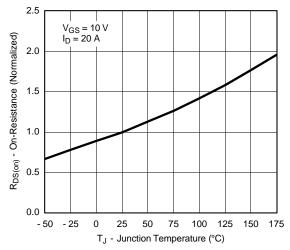
On-Resistance vs. Drain Current



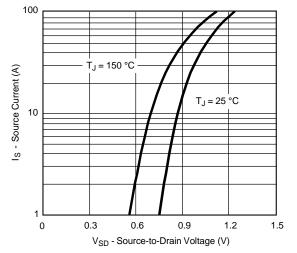
Gate Charge



TYPICAL CHARACTERISTICS (25 °C unless noted)



On-Resistance vs. Junction Temperature

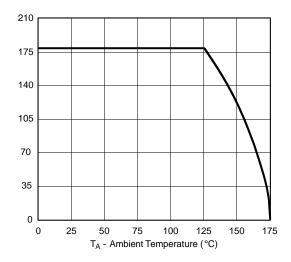


Source-Drain Diode Forward Voltage



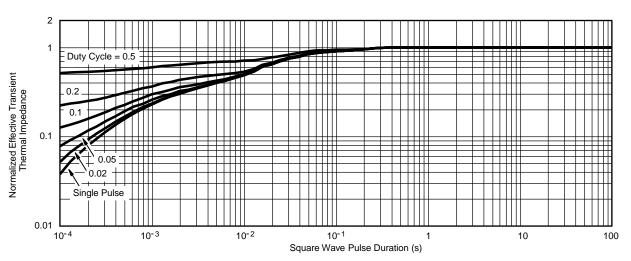


THERMAL RATINGS



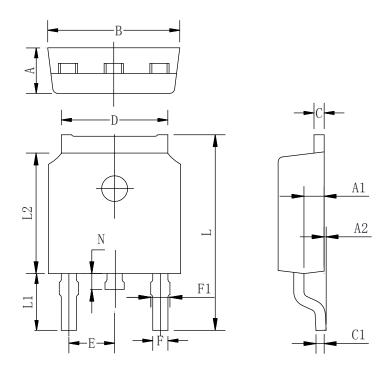
1000_F Limited by 10 µs 100 I_D - Drain Current (A) 100 µs 10 1 ms 10 ms 100 ms DC T_C = 25 °C Single Pulse 0.1 0.01 - 0.1 100 $V_{DS} - Drain-to-Source \ Voltage \ (V) \\ ^*V_{GS} > minimum \ V_{GS} \ at \ which \ R_{DS(on)} \ is \ specified$ Safe Operating Area

Maximum Drain Current vs. Ambient Temperature



Normalized Thermal Transient Impedance, Junction-to-Case

TO-252-2L PACKAGE OUTLINE



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

Symbol	Min	Тур	Max		
A	2.10	2.30	2.50		
A1	0.88	1.01	1.16		
A2	0.00	0.15	0.28		
В	6.40	6.60	6.80		
С	0.42	0.50	0.63		
C1	0.42	0.50	0.63		
D	5.08	5.32	5.65		
Е	2.286 TYP				
F	0.63	0.76	0.89		
F1	0.64	0.86	1.08		
L	9.30	9.90	10.80		
L1	2.4	2.8	3.6		
L2	5.90	6.10	6.55		
N	0.57	0.80	1.05		

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